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IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method for depositing a layer on a substrate, ~~wherein a~~ comprising:

introducing a substrate ~~(1; 101) is introduced~~ into a processing chamber ~~(2; 102)~~; ~~wherein~~

generating at least one plasma ~~(P) is generated~~ by at least one plasma cascade source ~~(3; 103)~~; ~~wherein~~

depositing at least one deposition material ~~(A) is deposited~~ on the substrate ~~(1; 101)~~ under the influence of the plasma; ~~(P), characterized in that for~~ and

manufacturing a catalyst layer by depositing at least a second deposition material ~~(B) is deposited~~ on the substrate ~~(101)~~ by at least a second plasma cascade source, a plasma source, a vapor deposition source and/or a sputtering source ~~(121)~~.

2. (Currently amended) A method according to claim 1, wherein said deposition material ~~(A,B)~~ is supplied outside the at least one plasma source ~~(3; 103)~~ into the processing chamber ~~(2; 102)~~, ~~preferably~~ such as to the plasma [[(P)]] in the processing chamber.

3. (Currently amended) A method according to claim 1 [[or 2]], wherein at least one volatile compound of said deposition material ~~(A, B)~~ is supplied to the plasma [[(P)]] for the ~~purpose of the~~ deposition.

4. (Currently amended) A method according to claim 3, wherein the volatile compound contains at least one precursor material which decomposes in the processing chamber ~~(2; 102)~~ in material to be deposited, before the material has reached the substrate ~~(1;101)~~.

5. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein at least one sputtering electrode [[(6)]] which comprises said deposition material [[(A, B)]] is arranged in the processing chamber [[(2)]], and the plasma [[(P)]] is contacted with each sputtering electrode [[(6)]] to sputter the substrate [[(I)]] with the material [[(A, B)]] of the electrode [[(6)]].

6. (Currently amended) A method according to claim 5, wherein the plasma [[(P)]] is passed at least partly through at least one passage of the at least one sputtering electrode [[(6)]] to contact the plasma with the electrode [[(6)]].

7. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein said deposition material comprises at least one catalyst material [[(A)]] which, whether or not after an activation treatment such as [[a]] reducing [[step]], is catalytically active.

8. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein said deposition material comprises at least one carrier material [[(B)]], which material is ~~inherently~~ initially, or after a further treatment, suitable to carry catalyst material.

9. (Currently amended) A method according to ~~claims 7 and~~ claim 8, wherein the at least one catalyst material [[(A)]] and the at least one carrier material [[(B)]] are deposited on the substrate [[(101)]] by different sources ~~(103, 103',121,121.')~~.

10. (Currently amended) A method according to ~~at least claims~~ claim 5~~, 7 and 8~~, wherein the at least one sputtering electrode [[(6)]] contains at least a part of both [[said]] a catalyst material [[(A)]] and [[said]] a carrier material [[(B)]].

11. (Currently amended) A method according to claim 10, wherein the sputtering electrode [[(6)]] contains compressed powders of said catalyst and carrier materials [[(A, B)]] to be deposited on the substrate [[(1)]].

12. (Currently amended) A method according to ~~at least~~ claim 10, wherein the at least one sputtering electrode [[(6)]] contains an alloy of said catalyst material [[(A)]] and said carrier material [[(B)]].

13. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate [[(101)]] comprises sheet material.

14. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate [[(101)]] is moved in the processing chamber [[(102)]] at least in such a way that each time a different part of the substrate [[(101)]] makes contact with the plasma [[(P)]].

15. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate [[(101)]] is brought from an environment into the processing chamber [[(102)]] and is discharged from the processing chamber [[(102)]] to the environment while the deposition material is deposited on the substrate [[(101)]] in the processing chamber [[(102)]].

16. (Currently amended) A method according to ~~at least~~ claim 1, wherein the substrate ~~(1; 101)~~ is substantially non-porous.

17. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate ~~(1; 101)~~ comprises at least one carrier material [[(B)]].

18. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate ~~(1;101)~~ comprises at least one metal and/or alloy.

19. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate ~~(1;101)~~ comprises Fecralloy.

20. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate ~~(1; 101)~~ comprises corrugated material.

21. (Currently amended) A method according to ~~at least~~ claim 1, wherein the substrate ~~(1; 101)~~ is substantially porous.

22. (Currently amended) A method according to ~~at least~~ claim 8, wherein said carrier material [[(B)]] comprises a metal.

23. (Currently amended) A method according to ~~at least~~ claim 8, wherein said carrier material [[(B)]] comprises an oxidized metal.

24. (Currently amended) A method according to ~~at least~~ claim 8, wherein said carrier material [[(B)]] comprises a semiconductor.

25. (Currently amended) A method according to ~~at least~~ claim 8, wherein said carrier material [[(B)]] comprises an oxidized semiconductor.

26. (Currently amended) A method according to claim 23 ~~and/or 25~~, wherein the carrier material [[(B)]] further contains a heat-conducting material~~, such as carbon~~.

27. (Currently amended) A method according to ~~at least~~ claim 7, wherein the at least one catalyst material [[(A)]] comprises nickel, copper, palladium, rhodium, platinum [[and/]]or iron or any combination thereof.

28. (Currently amended) A method according to ~~at least claims~~ claim 7 ~~and 8~~, wherein the deposition material [[(A, B)]] is deposited such that the chemical composition of the deposited material measured over ~~distances of 5 cm, preferably over~~ a distance of ~~10 cm, more particularly over a distance of~~ 20 cm, and differs by less than 10%~~, in particular less than 50% and more particularly less than 1%~~.

29. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein [[a]] reducing [[step]] is carried out at an elevated temperature for the purpose of reduction of the deposition material [[(A)]] deposited on the substrate [[(1; 101)]].

30. (Currently amended) A method according to claim 29, wherein the reducing [[step]] is carried out under the influence of hydrogen.

31. (Currently amended) A method according to claim 30, wherein an inert gas~~, such as nitrogen or argon,~~ which contains hydrogen[[,]] is supplied to the substrate [[(1; 101)]] for the purpose of the reduction.

32. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate ~~(1; 101)~~ is adjusted to a particular electrical potential~~, for instance~~ by DC, pulsed DC and/or RF biasing.

33. (Currently amended) A method according to ~~any one of the preceding claims~~ claim 1, wherein the substrate ~~(1; 101)~~ is adjusted to a ~~particular~~ treatment temperature.

34. (Currently amended) An apparatus for depositing a layer on a substrate~~, wherein the apparatus is provided with~~ comprising:

at least one plasma cascade source ~~(3; 103)~~ to generate at least one plasma ~~(P), the apparatus comprising means (6, 7) for bringing~~ ;

a first deposition material source configured to bring a first deposition material [[(A)]] into each plasma; ~~(P), the apparatus being further provided with~~

a substrate ~~positioning means (8; 118)~~ positioner to bring and/or keep at least a part of a substrate ~~(1; 101)~~ in such a position in a processing chamber ~~(2;102)~~ that the substrate ~~(1; 101)~~ makes contact with said plasma ~~(P) characterized in that, for manufacturing a catalyst, the apparatus comprises~~; and

a second plasma cascade source, a plasma source, a vapor deposition source and/or a sputtering source ~~(121) for depositing~~ configured to deposit at least a second deposition material [[(B)]] on the substrate [[(101)]].

35. (Currently amended) An apparatus according to claim 34, wherein the first deposition material source comprises ~~apparatus is provided with~~ at least one sputtering electrode [[(6)]] which contains deposition material [[(A, B)]] to be deposited, wherein the sputtering electrode is positioned such that the plasma [[(P)]] generated by the at least one plasma source [[(3)]] during use sputters material [[(A, B)]] from the sputtering electrode [[(6)]] on the substrate [[(1)]].

36. (Currently amended) An apparatus according to claim 35, wherein each sputtering electrode [[(6)]] is arranged downstream of the at least one plasma source [[(3)]], [[while]] and at least one sputtering electrode [[(6)]] is provided with at least one plasma passage to allow the plasma [[(P)]] to pass from the source [[(3)]] to the substrate[[(1)]].

37. (Currently amended) An apparatus according to claim 35[[or 36]], wherein the sputtering electrode [[(6)]] lies against the source [[(3)]].

38. (Currently amended) An apparatus according to ~~any one of claims 34~~ claim 37, wherein the ~~apparatus is provided with~~ first deposition material source comprises at least one fluid supply channel ~~(7; 120)~~ to supply a material to be deposited, being in a volatile state, to the plasma [[(P)]].

39. (Currently amended) An apparatus according to ~~at least claims 35 and 38~~ claim 38, wherein the at least one sputtering electrode [[(6)]] is provided with said fluid supply channel.

40. (Currently amended) An apparatus according to ~~at least~~ claim 34, wherein the apparatus is provided with at least two plasma cascade sources ~~(103, 103')~~ to generate at least two plasmas [[(P, P')]], wherein these plasma cascade sources ~~(103,103')~~ and the substrate ~~positioning means (118, 118')~~ positioner are positioned such that opposite sides of the substrate ~~(1; 101)~~ during use make contact with the plasmas [[(P, P')]]generated by [[those]] the two plasma cascade sources ~~(103, 103')~~ to deposit material an the opposite sides of the substrate [[(101)]].

41. (Currently amended) An apparatus according to ~~at least~~ claim 34, wherein the apparatus is provided with a substrate supply roller ~~(110)~~ and a discharge roller ~~(111)~~, respectively, [[for]] to supply and discharge, respectively, [[of]] a substrate [[(101)]] that can be rolled up, such as a web and/or sheet-like substrate, to and from the processing chamber [[(101)]], respectively.

42. (Currently amended) An apparatus according to ~~at least~~ claim 34, wherein a wall [[(104)]] of the processing chamber [[(102)]] is provided with at least one passage [[(105)]] to pass the substrate [[(101)]] into and/or out of that chamber [[(102)]].

43. (Currently amended) An apparatus according to claim 42, wherein at least a part of the at least one passage [[(105)]] of the processing chamber wall [[(104)]] is bounded by oppositely arranged feed-through rollers [[(106)]], ~~which~~ and the feed-through rollers

[[(106)]] are arranged to engage a part of the substrate [[(101)]] disposed between them during use, for the purpose of feed-through of the substrate [[(101)]].

44. (Currently amended) An apparatus according to ~~at least~~ claim 41, wherein the apparatus is provided with a pair of rollers ~~deformation means (112)~~ to deform the substrate [[(101)]] which has unrolled from the supply roller [[(110)]].

45. (Currently amended) An apparatus according to claim 44, wherein the ~~deformation means (112)~~ pair of rollers are arranged to corrugate and/or serrate the substrate [[(101)]].

46. (Currently amended) An apparatus according to ~~at least~~ claim 34, wherein the apparatus is provided with ~~means for vapor depositing material~~ a vapor deposition apparatus to vapor deposit material on the substrate ~~(1;101)~~.

47. (Currently amended) An apparatus according to ~~at least~~ claim 34, wherein the apparatus is provided with at least one separate sputtering source ~~(121) for sputtering~~ configured to sputter material on the substrate [[(101)]].

48. (Currently amended) A catalyst provided with at least one carrier material [[(B)]] and at least one catalyst material [[(A)]], the carrier material comprising are oxidic material, and the carrier material further comprising at least one heat conducting material.

49. (Original) A catalyst according to claim 48, wherein the heat-conducting material comprises carbon.

50. (Currently amended) A catalyst manufactured according to ~~claim 48 or 49 obtained with a~~ the method ~~according to any~~ of claim 1 ~~claims 1-38~~.